**Product data sheet** 

## 1. General description

Dual Silicon Carbide Schottky diode in a TO247 plastic package, designed for high frequency switched-mode power supplies.



### 2. Features and benefits

- New 6th Generation Technology
- · Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability I<sub>FSM</sub>
- Reduced losses in associated MOSFET
- Reduced EMI
- · Reduced cooling requirements
- RoHS compliant
- AEC-Q101 qualified

## 3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- · Motor Drives
- On board charger

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		Values		Unit	
Absolute	Absolute maximum rating							
$V_{RRM}$	repetitive peak reverse voltage				650		V	
I <sub>O(AV)</sub>	limiting average forward current	$\delta$ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 133 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3		20		А		
T <sub>j</sub>	junction temperature			-55 to 175		°C		
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit	
Static ch	aracteristics							
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.26	1.40	V	
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.35	1.55	V	
Dynamic	Dynamic characteristics							
Q <sub>r</sub>	recovered charge	$I_F = 10 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$ ; per diode; Fig. 7		-	24	-	nC	

# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode	$\parallel$ $\circ$ $\parallel$	A1
3	A2	anode		K
mb	mb	mounting base; connected to cathode	1 2 3	sym125

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number		Small packing quantity	Package version	Package issue date
WNSC6D20650CW-A	TO247	WNSC6D20650CW-A6Q	Tube	30	SOT429	25-Mar-2013

# 7. Marking

## Table 4. Marking codes

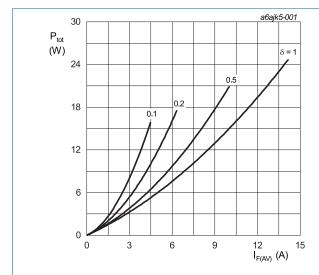
Type number	Marking codes
WNSC6D20650CW-A	WNSC6D 20650CW-A

# 8. Limiting values

**Table 5. Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
$V_R$	reverse voltage	DC		650	V
I <sub>O(AV)</sub>	limiting average forward current	δ = 0.5; square-wave pulse; T <sub>mb</sub> ≤ 133 °C; both diodes conducting; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		20	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 134 °C; square-wave pulse; per diode		20	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		75	А
		$t_p$ = 10 $\mu$ s; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode		800	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$		28.125	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature			-55 to 175	°C
T <sub>j</sub>	junction temperature			-55 to 175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 0.910 \text{ V; } R_{\text{s}} = 0.0588 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

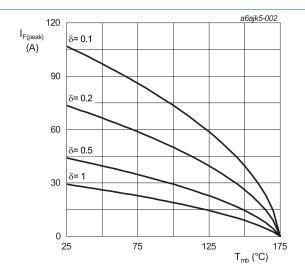
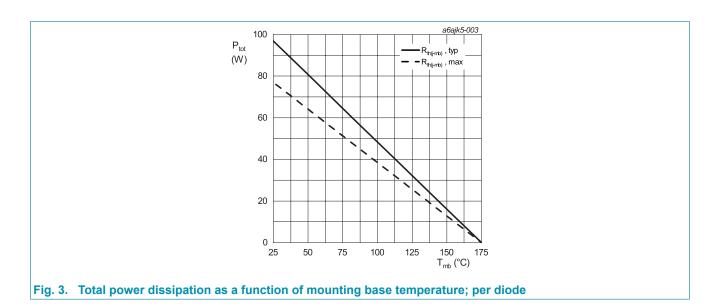


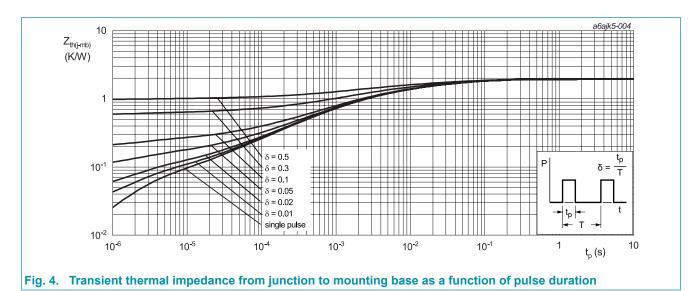
Fig. 2. Current derating as a function of mounting base temperature; per diode



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

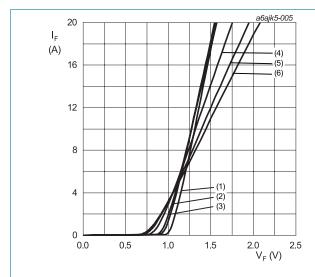
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance	per diode; Fig. 4		-	1.55	1.95	K/W
	from junction to mounting base	both diodes conducting		-	8.0	1	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W



## 10. Characteristics

#### Table 7 Characteristics

Table 7. Ci	iaracteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	racteristics						
$V_{F}$	forward current	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 5</u>		-	1.26	1.40	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; per diode; <u>Fig. 5</u>		-	1.35	1.55	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 5</u>		-	1.40	1.60	V
I <sub>R</sub>	reverse current	$V_R = 650 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	1	50	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 175 °C; per diode; <u>Fig. 6</u>		-	15	200	μA
Dynamic	characteristics						
Q <sub>r</sub>	recovered charge	$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; Fig. 7$		-	24	-	nC
$C_d$	diode capacitance	$f = 1 \text{ MHz}$ ; $V_R = 1 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode		-	500	-	pF
		$f = 1 \text{ MHz; } V_R = 300 \text{ V; } T_j = 25 \text{ °C; per diode}$		-	58	-	pF
		$f = 1 \text{ MHz}$ ; $V_R = 600 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode		-	52	-	pF
E <sub>as</sub>	non-repetitive avalanche energy	$I_R = 5 \text{ A}$ ; L = 5 mH; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; per diode		60	-	-	mJ



 $V_o$  = 0.910 V;  $R_s$  = 0.0588  $\Omega$ 

(1)  $T_j = -55$  °C; typical values

(2) T<sub>j</sub> = 0 °C; typical values

(3) T<sub>i</sub> = 25 °C; typical values

(4) T<sub>i</sub> = 100 °C; typical values

(5) T<sub>i</sub> = 150 °C; typical values

(6) T<sub>i</sub> = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

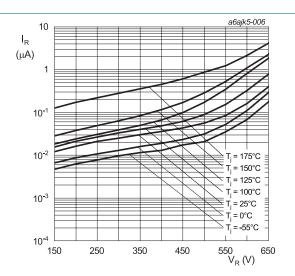


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

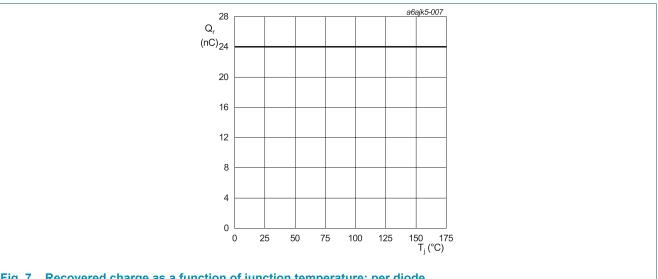
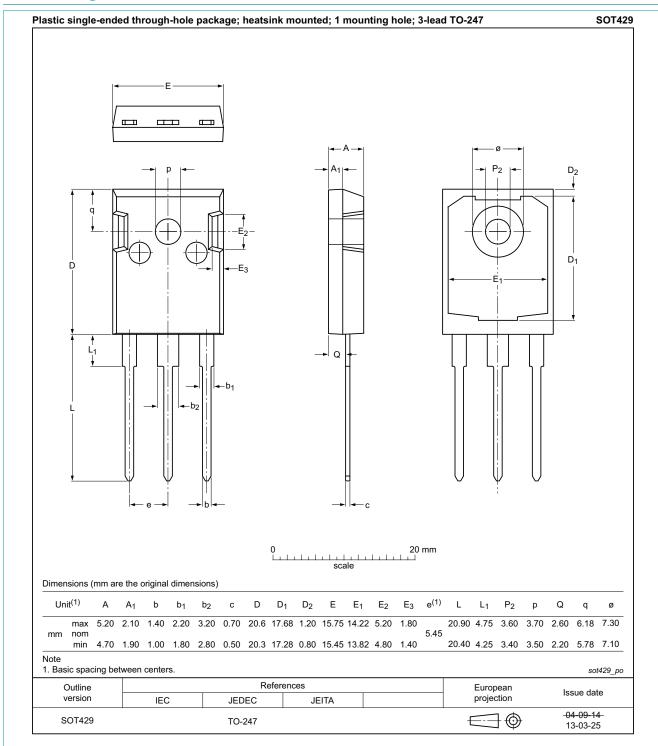


Fig. 7. Recovered charge as a function of junction temperature; per diode

# 11. Package outline



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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**Product data sheet** 

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